

Silicon PNP Power Transistors

2SA907/908/909

DESCRIPTION

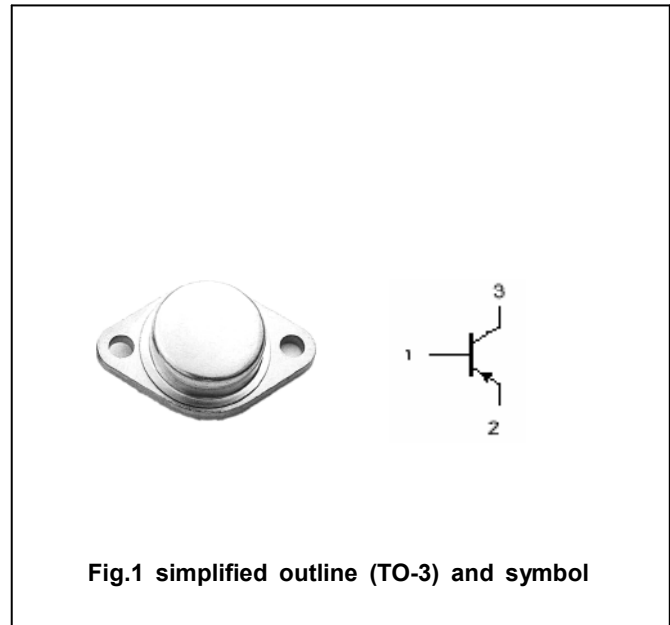
- With TO-3 package
- Complement to type 2SC1584/1585/1586

APPLICATIONS

- For power switching and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SA907	-100	V
		2SA908	-150	
		2SA909	-200	
V _{CEO}	Collector-emitter voltage	2SA907	-100	V
		2SA908	-150	
		2SA909	-200	
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-15	A
I _B	Base current		-5	A
P _C	Collector power dissipation	T _C =25□	150	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~150	□

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA907	I _C =-50mA ; I _B =0	-100			V
		2SA908		-150			
		2SA909		-200			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-10A; I _B =-1A			-3.0	V
I _{CBO}	Collector cut-off current	2SA907	V _{CB} =-100V; I _E =0			-1.0	mA
		2SA908	V _{CB} =-150V; I _E =0				
		2SA909	V _{CB} =-200V; I _E =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-6V; I _C =0			-1.0	mA
h _{FE}	DC current gain		I _C =-5A ; V _{CE} =-4V	30			
f _T	Transition frequency		I _C =-0.5A ; V _{CE} =-12V		10		MHz

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)